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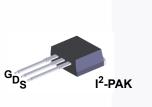
## FQI5N60C N-Channel QFET<sup>®</sup> MOSFET 600 V, 4.5 A, 2.5 Ω

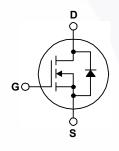
### Features

- 4.5 A, 600 V,  $R_{DS(on)}$  = 2.5  $\Omega$  (Max.)  $@V_{GS}$  = 10 V,  $I_D$  = 2.1 A
- Low Gate Charge (Typ. 15 nC)
- Low Crss (Typ. 6.5 pF)
- 100% Avalanche Tested

## Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.





## Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

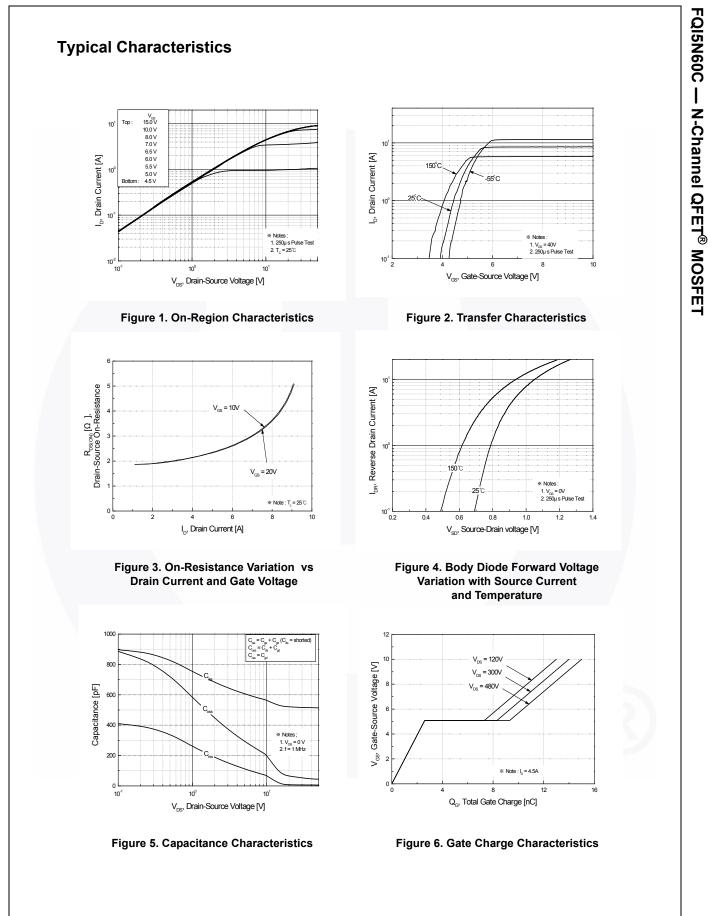
| Symbol                            | Parameter  |          | FQI5N60CTU  | Unit |
|-----------------------------------|--|----------|-------------|------|
| V <sub>DSS</sub>                  | Drain-Source Voltage   |          | 600         | V    |
| I <sub>D</sub>                    | Drain Current - Continuous ( $T_C = 25^{\circ}C$ )                               |          | 4.5         | A    |
|                                   | - Continuous (T <sub>C</sub> = 100°C)  |          | 2.6         | А    |
| I <sub>DM</sub>                   | Drain Current - Pulsed   | (Note 1) | 18          | A    |
| V <sub>GSS</sub>                  | Gate-Source Voltage  |          | ± 30        | V    |
| E <sub>AS</sub>                   | Single Pulsed Avalanche Energy (Note   |          | 210         | mJ   |
| I <sub>AR</sub>                   | Avalanche Current  | (Note 1) | 4.5         | A    |
| E <sub>AR</sub>                   | Repetitive Avalanche Energy  | (Note 1) | 10          | mJ   |
| dv/dt                             | Peak Diode Recovery dv/dt (Note 3)   |          | 4.5         | V/ns |
| D                                 | Power Dissipation ( $T_C = 25^{\circ}C$ )  |          | 100         | W    |
| P <sub>D</sub>                    | - Derate above 25°C  |          | 0.8         | W/°C |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Temperature Range  |          | -55 to +150 | °C   |
| Τ <sub>L</sub>                    | Maximum lead temperature for soldering purposes,<br>1/8" from case for 5 seconds |          | 300         | °C   |

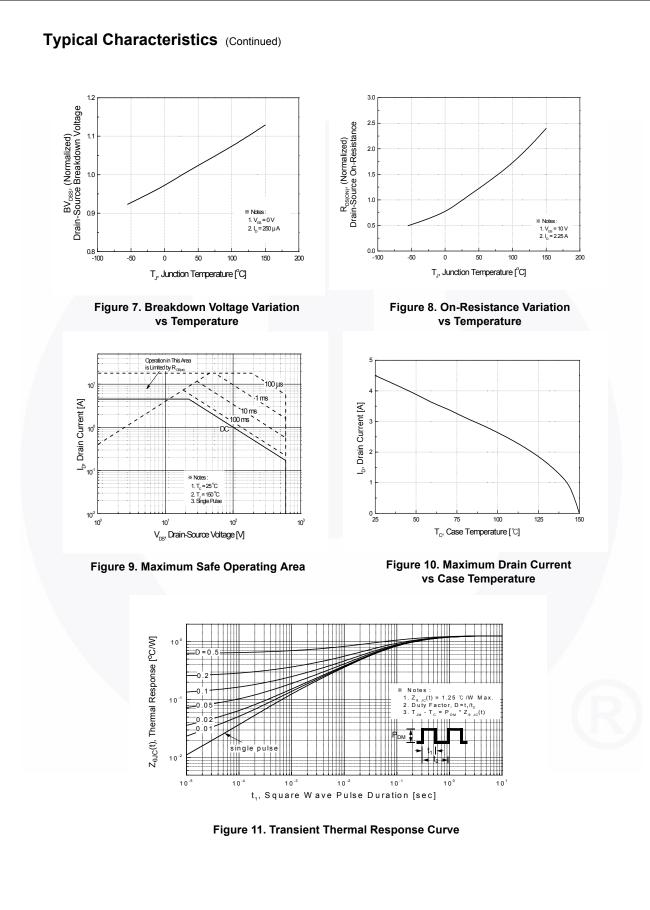
## **Thermal Characteristics**

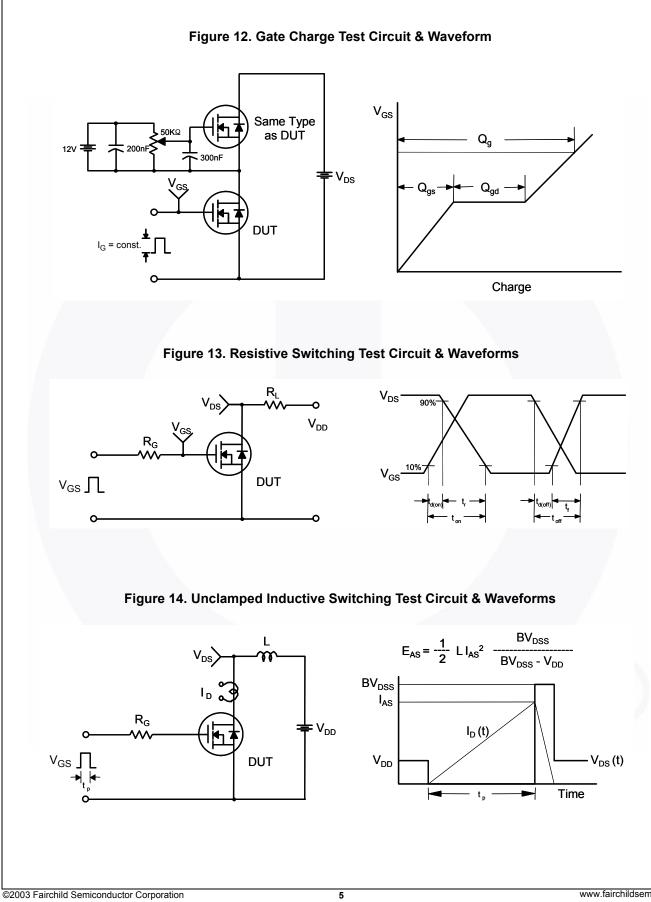
| Symbol                | Parameter                                     | FQI5N60CTU | Unit  |  |
|-----------------------|---|------------|-------|--|
| $R_{	extsf{	heta}JC}$ | Thermal Resistance, Junction-to-Case, Max.    | 1.25       | °C/W  |  |
| R <sub>θJA</sub>      | Thermal Resistance, Junction-to-Ambient, Max. | 62.5       | C/ VV |  |

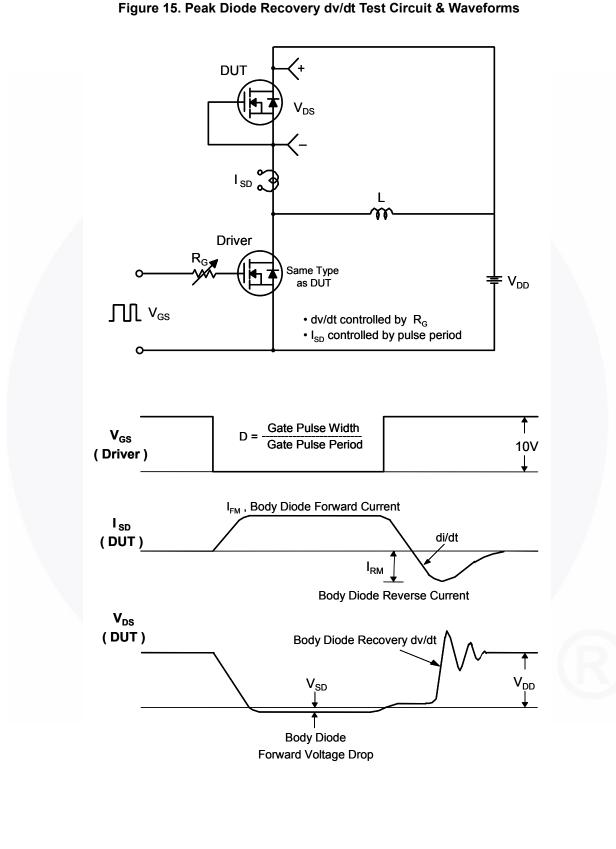
November 2013

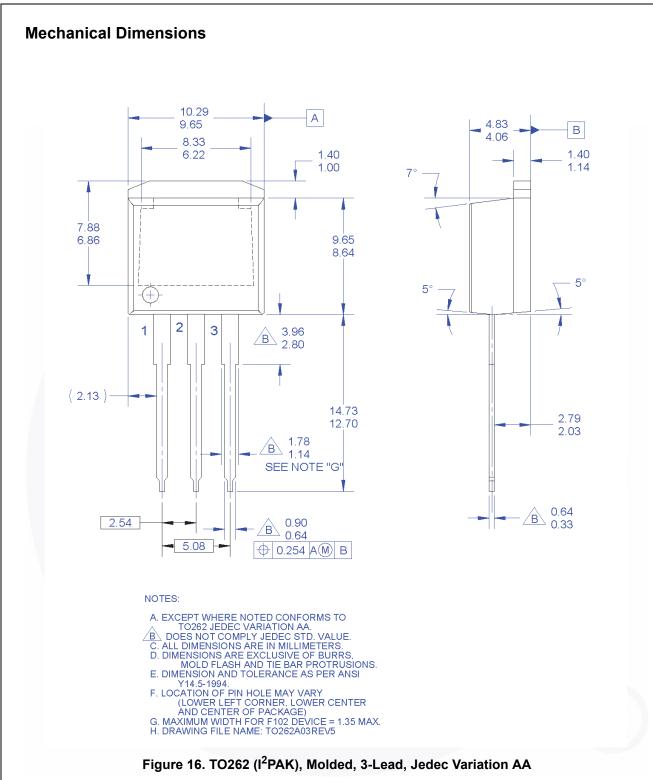
| Device MarkingDeviceFQI5N60CFQI5N60CTU |   | PackageReel SizeI2-PAKTube   |  | Таре  | Width | Qua        | intity |          |
|--|---|--|--|---|-------|------------|--------|----------|
|  |   |  |  | N/A   |       | 50 units   |        |          |
| lectri                                 | cal Chara                               | acteristics T <sub>c</sub> = 25°C  | C unless otherwise   | noted.  |       |            |        |          |
| Symbol                                 |   | Parameter  | Test Conditions  |   | Min   | Тур        | Max    | Unit     |
| רף<br>סנו ביי                          | racteristi                              |  |  |   |       |            |        |          |
| BV <sub>DSS</sub>                      |   | ce Breakdown Voltage   | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA   |   | 600   |            |        | V        |
| ABV <sub>DSS</sub>                     |   | ů.   |  |   | 000   |            |        | •        |
| ΔT <sub>J</sub>                        | ů i                                     |  | $I_D$ = 250 $\mu$ A, Referenced to 25°C  |   |       | 0.6        |        | V/°C     |
|  | Zara Cata )                             | Altere Ducin Current   | $V_{DS}$ = 600 V, $V_{GS}$ = 0 V<br>$V_{DS}$ = 480 V, $T_{C}$ = 125°C                    |   |       |            | 1      | μA       |
| DSS                                    | Zero Gate                               | /oltage Drain Current  |  |   |       | -          | 10     | μA       |
| GSSF                                   | Gate-Body                               | Leakage Current, Forward   | $V_{GS}$ = 30 V, $V_{DS}$  | = 0 V   |       |            | 100    | nA       |
| GSSR                                   | Gate-Body                               | Leakage Current, Reverse   | $V_{GS}$ = -30 V, $V_{DS}$   | <sub>5</sub> = 0 V  |       |            | -100   | nA       |
| )n Cha                                 | racteristic                             | 25   |  |   |       |            |        |          |
| / <sub>GS(th)</sub>                    | 1                                       | hold Voltage   | $V_{DS} = V_{GS}, I_D = 1$   | 250 μA  | 2.0   |            | 4.0    | V        |
| R <sub>DS(on)</sub>                    | Static Drain-Source<br>On-Resistance    |  | V <sub>GS</sub> = 10 V, I <sub>D</sub> =   | 2.25 A  |       | 2.0        | 2.5    | Ω        |
| FS                                     | Forward Tra                             | ansconductance   | V <sub>DS</sub> = 40 V, I <sub>D</sub> =   | 2.25 A  |       | 4.7        |        | S        |
| Dynam<br><sub>Piss</sub>               | ic Charact                              |  | <u> </u>   | - 0)/   |       | 515        | 670    | pF       |
| YOSS                                   | Output Cap                              |  | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,<br>f = 1.0 MHz                            |   |       | 55         | 72     | pF       |
| rss                                    |   | ansfer Capacitance   |  |   |       | 6.5        | 8.5    | pF       |
|  |   | -  |  |   |       |            |        | I.       |
|  | ng Charao                               |  |  |   |       | 10         |        |          |
| d(on)                                  | Turn-On De                              | ,  | V <sub>DD</sub> = 300 V, I <sub>D</sub> =  | $V_{DD}$ = 300 V, I <sub>D</sub> = 4.5A,<br>R <sub>G</sub> = 25 Ω |       | 10         | 30     | ns       |
|  | Turn-On Ris                             |  | R <sub>G</sub> = 25 Ω  |   |       | 42         | 90     | ns       |
| d(off)                                 | Turn-Off De                             | ,  | (Note 4)   |   |       | 38         | 85     | ns       |
|  | Turn-Off Fa                             |  |  | · · ·   |       | 46         | 100    | ns       |
| 2 <sup>g</sup>                         | Total Gate (                            | -  | V <sub>DS</sub> = 480 V, I <sub>D</sub> =  | = 4.5A,   |       | 15         | 19     | nC       |
| 2 <sub>gs</sub>                        | Gate-Sourc<br>Gate-Drain                | U  | $V_{GS} = 10 V$ (Note 4)   |   |       | 2.5<br>6.6 |        | nC<br>nC |
| 2 <sub>gd</sub>                        | Gale-Dialit                             | Charge   |  | (Note 4)  |       | 0.0        |        | no       |
| )rain-S                                | ource Dio                               | de Characteristics a   | nd Maximum F   | Ratings   |       |            |        |          |
| 3                                      |   | Continuous Drain-Source Dic  |  | -   |       |            | 4.5    | A        |
| SM                                     | Maximum Continuous Drain-Source Diode F |  |  |   |       |            | 18     | A        |
| / <sub>SD</sub>                        |   | ce Diode Forward Voltage   | $V_{GS} = 0 V, I_{S} = 4.5 A$ $V_{GS} = 0 V, I_{S} = 4.5 A,$ $dI_{F} / dt = 100 A/\mu s$ |   |       |            | 1.4    | V        |
| r                                      |   | ecovery Time   |  |   |       | 300        |        | ns       |
| ۶ <sub>rr</sub>                        | Reverse Re                              | ecovery Charge   |  |   |       | 2.2        |        | μC       |
| TES:                                   | I                                       |  |  | Į   |       |            |        |          |
|  | ating : Pulse widt                      | h limited by maximum junction temper   | rature.  |   |       |            |        |          |
| 10.0                                   |   | $_{\rm O}$ = 50V, R <sub>G</sub> = 25 $\Omega$ , starting T <sub>J</sub> = 25° | C  |   |       |            |        |          |











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FQI5N60C — N-Channel QFET<sup>®</sup> MOSFET



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|                                      |                                     |  |   |
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